Am27C4096

Advanced Micro Devices

4 Megabit (262,144 x 16-Bit) CMOS EPROM

DISTINCTIVE CHARACTERISTICS

- Fast access time
 - 90 ns
- Low power consumption
 - 100 μA maximum CMOS standby current
- JEDEC-approved pinout
 - Plug in upgrade of 1 Mbit and 2 Mbit EPROMs
 - 40-pin DIP/PDIP
 - 44-pin LCC/PLCC

- Single + 5 V power supply
- ± 10% power supply tolerance standard on most speeds
- 100% FlashriteTM programming
 - Typical programming time of 32 seconds
- Latch-up protected to 100 mA from -1 V to Vcc + 1 V
- High noise immunity

GENERAL DESCRIPTION

The Am27C4096 is a 4 Mbit ultraviolet erasable programmable read-only memory. It is organized as 256K words by 16 bits per word, operates from a single +5 V supply, has a static standby mode, and features fast single address location programming. The Am27C4096 is ideal for use in 16-bit microprocessor systems. Products are available in windowed ceramic DIP and LCC packages as well as plastic one time programmable (OTP) PDIP and PLCC packages.

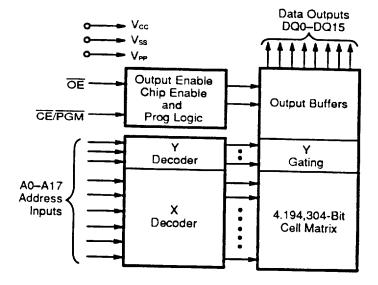
Typically, any byte can be accessed in less than 90 ns, allowing operation with high-performance microprocessors without any WAIT states. The Am27C4096 offers separate Output Enable (OE) and Chip Enable (OE)

controls, thus eliminating bus contention in a multiple bus microprocessor system.

AMDs CMOS process technology provides high speed, low power, and high noise immunity. Typical power consumption is only 125 mW in active mode, and 125 μ W in standby mode.

All signals are TTL levels, including programming signals. Bit locations may be programmed singly, in blocks, or at random. The Am27C4096 supports AMD's Flashrite programming algorithm (100 µs pulses) resulting in typical programming times of 32 seconds.

BLOCK DIAGRAM



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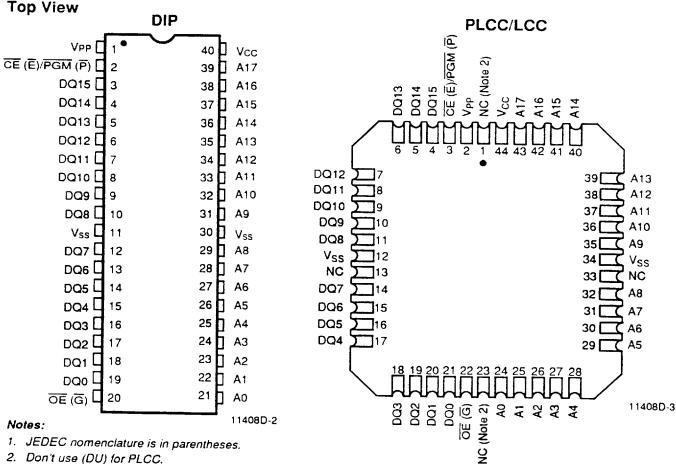
Publication# 11408 Rev. D Amendment/0 Issue Date: July 1994

0257528 0033007 205

PRODUCT SELECTOR GUIDE

Family Part No.	Am27C4096						
Ordering Part No:			I			<u> </u>	
Vcc ± 5%	-95	-105					
Vcc ±10%		-100	-120	-150	-200	-250	
Max Access Time (ns)	90	100	120	150	200	250	
CE (E) Access Time (ns)	90	100	120	150	200	250	
OE (G) Access Time (ns)	50	50	50	65	75	100	

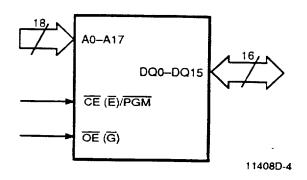
CONNECTION DIAGRAMS



PIN DESIGNATIONS

A0-A17 = Address inputs CE (B/PGM (P) = Chip Enable Input DQ0-DQ15 = Data Input/Outputs DU No External Connection NC = No Internal Connection OE (G) = Output Enable Input Vcc = Vcc Voltage Input VPP = Program Voltage Input

LOGIC SYMBOL



Vss

2

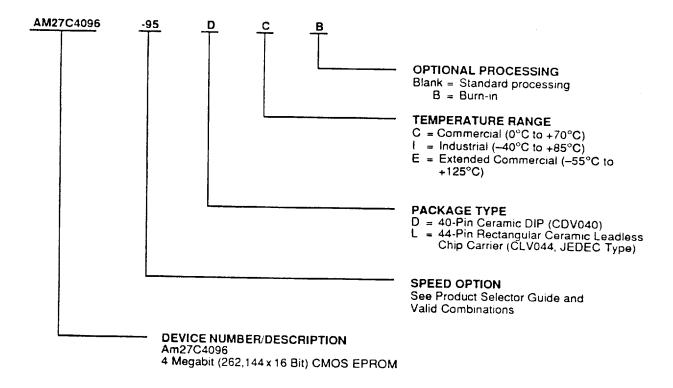
Am27C4096

0257528 0033008 141 1

= Ground

ORDERING INFORMATION EPROM Products

AMD standard products are available in several packages and operating ranges. The order number (Valid Combination) is



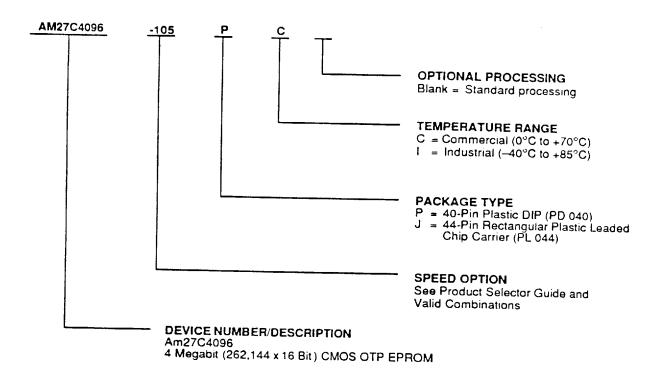
Valid Combinations						
AM27C4096-95	DC, DCB					
AM27C4096-100 AM27C4096-105	DC, DCB, DI, DIB					
AM27C4096-120	DC, DCB, DE,					
AM27C4096-150	DEB, DI, DIB, LC, LCB, LI,					
AM27C4096-200	LIB. LE, LEB					

Valid Combinations

Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations and to check on newly released combinations.

ORDERING INFORMATION OTP Products

AMD standard products are available in several packages and operating ranges. The order number (Valid Combination) is



Valid Combinations						
AM27C4096-105	PC, JC					
AM27C4096-120						
AM27C4096-150	PC, JC, PI, JI					
AM27C4096-200						

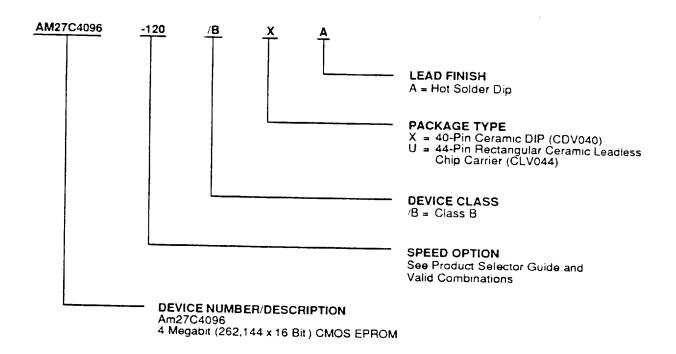
Valid Combinations

Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations and to check on newly released combinations.

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MILITARY ORDERING INFORMATION Military APL Products

AMD products for Aerospace and Defense applications are available in several packages and operating ranges. APL (Approved Products List) products are fully compliant with MIL-STD-883 requirements. The order number (Valid Combination) is formed by a combination of:



Valid Combinations					
AM27C4096-120					
AM27C4096-150	/BXA, /BUA				
AM27C4096-200	, DAA, /BUA				
AM27C4096-250					

Valid Combinations

Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations and to check on newly released combinations.

Group A Tests

Group A tests consist of Subgroups 1, 2, 3, 7, 8, 9, 10, 11.

FUNCTIONAL DESCRIPTION

Erasing The Am27C4096

In order to clear all locations of their programmed contents, it is necessary to expose the Am27C4096 to an ultraviolet light source. A dosage of 15 W seconds/cm₂ is required to completely erase an Am27C4096. This dosage can be obtained by exposure to an ultraviolet lamp—wavelength of 2537 Å—with intensity of 12,000 μW/cm² for 15 to 20 minutes. The Am27C4096 should be directly under and about one inch from the source and all filters should be removed from the UV light source prior to erasure.

It is important to note that the Am27C4096 and similar devices will erase with light sources having wavelengths shorter than 4000 Å. Although erasure times will be much longer than with UV sources at 2537 Å, exposure to fluorescent light and sunlight will eventually erase the Am27C4096 and exposure to them should be prevented to realize maximum system reliability. If used in such an environment, the package window should be covered by an opaque label or substance.

Programming the Am27C4096

Upon delivery or after each erasure the Am27C4096 has all 4,194,304 bits in the "ONE" or HIGH state. "ZE-ROs" are loaded into the Am27C4096 through the procedure of programming.

The programming mode is entered when 12.75 V ± 0.25 V is applied to the V_{PP} pin, CE/PGM is at V_{IL} and OE is at V_{IH}.

For programming, the data to be programmed is applied 16 bits in parallel to the data output pins.

The Flashrite algorithm reduces programming time by using 100 µs programming pulses and by giving each address only as many pulses as are necessary in order to reliably program the data. After each pulse is applied to a given address, the data in that address is verified. If the data does not verify, additional pulses are given until it verifies or the maximum is reached. This process is repeated while sequencing through each address of the Am27C4096. This part of the algorithm is done at Vcc = 6.25 V to assure that each EPROM bit is programmed to a sufficiently high threshold voltage. After the final address is completed, the entire EPROM memory is verified at Vcc = Vpp = 5.25 V.

Please refer to Section 6 for programming flow chart and characteristics

Program Inhibit

Programming of multiple Am27C4096 in parallel with different data is also easily accomplished. Except for $\overline{\text{CE/PGM}}$, all like inputs of the parallel Am27C4096 may be common. A TTL low-level program pulse applied to an Am27C4096 $\overline{\text{CE/PGM}}$ input with VPP = 12.75 V \pm

0.25 V and OEHIGH will program that Am27C4096. A high-level CE/PGM input inhibits the other Am27C4096 devices from being programmed.

Program Verify

A verify should be performed on the programmed bits to determine that they were correctly programmed. The verify should be performed with \overline{OE} at V_{IL} , $\overline{CE/PGM}$ at V_{IH} , and V_{PP} between 12.5 V and 13.0 V.

Auto Select Mode

The auto select mode allows the reading out of a binary code from an EPROM that will identify its manufacturer and type. This mode is intended for use by programming equipment for the purpose of automatically matching the device to be programmed with its corresponding programming algorithm. This mode is functional in the $25^{\circ}\text{C} \pm 5^{\circ}\text{C}$ ambient temperature range that is required when programming the Am27C4096.

To activate this mode, the programming equipment must force 12.0 V \pm 0.5 V on address line A9 of the Am27C4096. Two identifier bytes may then be sequenced from the device outputs by toggling address line A0 from V_{IL} to V_{IH}. All other address lines must be held at V_{IL} during auto select mode.

Byte 0 (A0 = V_{IL}) represents the manufacturer code, and byte 1(A0 = V_{IH}), the device identifier code. For the Am27C4096, these two identifier bytes are given in the Mode Select Table. All identifiers for manufacturer and device codes will possess odd parity, with the MSB (DQ7) defined as the parity bit.

Read Mode

The Am27C4096 has two control functions, both of which must be logically satisfied in order to obtain data at the outputs. Chip Enable (CE/PGM) is the power control and should be used for device selection. Output Enable (OE) is the output control and should be used to gate data to the output pins, independent of device selection. Assuming that addresses are stable, address access time (tAcc) is equal to the delay from CE/PGM to output (tce). Data is available at the outputs toe after the falling edge of OE, assuming that CE/PGM has been LOW and addresses have been stable for at least tacc—toe.

Standby Mode

The Am27C4096 has a CMOS standby mode which reduces the maximum Vcc current to 100 μ A. It is placed in CMOS-standby when $\overline{\text{CE/PGM}}$ is at Vcc \pm 0.3 V. The Am27C4096 also has a TTL-standby mode which reduces the maximum Vcc current to 1.0 mA. It is placed in TTL-standby when $\overline{\text{CE/PGM}}$ is at ViH. When in standby mode, the outputs are in a high-impedance state, independent of the $\overline{\text{OE}}$ input.

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Output OR-Tieing

To accommodate multiple memory connections, a twoline control function is provided to allow for:

- Low memory power dissipation
- Assurance that output bus contention will not occur

It is recommended that $\overline{\text{CE/PGM}}$ be decoded and used as the primary device-selecting function, while $\overline{\text{OE}}$ be made a common connection to all devices in the array and connected to the READ line from the system control bus. This assures that all deselected memory devices are in low-power standby mode and that the output pins are only active when data is desired from a particular memory device.

System Applications

During the switch between active and standby conditions, transient current peaks are produced on the rising and falling edges of Chip Enable. The magnitude of these transient current peaks is dependent on the output capacitance loading of the device. At a minimum, a $0.1-\mu F$ ceramic capacitor (high frequency, low inherent inductance) should be used on each device between Vcc and Vss to minimize transient effects. In addition, to overcome the voltage drop caused by the inductive effects of the printed circuit board traces on EPROM arrays, a $4.7-\mu F$ bulk electrolytic capacitor should be used between Vcc and Vss for each eight devices. The location of the capacitor should be close to where the power supply is connected to the array.

MODE SELECT TABLE

Mode	Pins	CE/PGM	ŌĒ	AO	Α9	Vpp	Outputs
Read		Vic	V _{it.}	Х	Х	Х	Ооит
Output Disa	able	Vıı	ViH	X	X	X	Hi–Z
Standby (T	TL)	ViH	Х	X	X	X	Hi–Z
Standby (C	MOS)	V _{cc} ± 0.3 V	X	X	Х	Х	Hi–Z
Program		Vit	ViH	Х	Х	Vpp	Din
Program Ve		ViH	VıL	Х	×	Vpp	Dout
Program Inhibit		ViH	ViH	Х	×	Vpp	Hi-Z
Auto Select	Manufacturer Code	VıL	VıL	Vін	VH	Х	O1H
(Note 3)	Device Code	VıL	ViL	ViH	VH	Х	19H

Notes:

- 1 $X = Either V_{H} or V_{U}$
- 2. VH = 12.0 V ± 0.5 V
- 3. $A1-A8 = A10-A17 = V_{IL}$
- 4. See DC Programming Characteristics for VPP voltage during programming.

ABSOLUTE MAXIMUM RATINGS

Storage Temperature:
OTP Products
All Other Products65°C to +150°C
Ambient Temperature
with Power Applied55°C to +125°C
Voltage with Respect to Vss:
All pins except A9. VPP,
and Vcc (Note 1)0.6 V to Vcc + 0.6 V
A9 and V _{PP} (Note 2)0.6 V to 13.5 V
Vcc0.6 V to 7.0 V

Notes:

- 1. During transitions, the inputs may overshoot $V_{\rm SS}$ to -2.0~V for periods of up to 20 ns. Maximum DC voltage on input and I/O may overshoot to $V_{\rm CC}$ + 2.0 V for periods of up to 20 ns.
- 2. During transitions. A9 and VPP may overshoot Vss to -2.0 V for periods of up to 20 ns. A9 and VPP must not exceed 13.5 V for any period of time.

Stresses above those listed under Absolute Maximum Ratings may cause permanent device failure. Functionality at or above these limits is not implied. Exposure to absolute maximum ratings for extended periods may affect device reliability.

OPERATING RANGES

Commercial (C) Devices Case Temperature (Tc) 0°C to +70°C
Industrial (I) Devices Case Temperature (Tc)40°C to +85°C
Extended Commercial (E) Devices Case Temperature (Tc) -55°C to +125°C
Military (M) Devices Case Temperature (Tc)55°C to +125°C
Supply Read Voltages: Vcc for Am27C4096-XX5 +4.75 V to +5.25 V Vcc for Am27C4096-XX0 +4.50 V to +5.50 V
100 101 1 111127 0 1000 XXX0

Operating ranges define those limits between which the functionality of the device is guaranteed.

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DC CHARACTERISTICS over operating range unless otherwise specified. (Notes 1, 2 and 4) (for APL Products, Group A, Subgroups 1, 2, 3, 6, and 7 are tested unless otherwise noted)

Parameter Symbol	Parameter Description	Test Conditions		Min	Max	Unit
Vон	Output HIGH Voltage	loн = 400 µA		2.4		
Vol	Output LOW Voltage	loL = 2.1 mA			0.45	
ViH	Input HIGH Voitage			2.0	Vcc +0.5	
VIL	Input LOW Voltage			-0.5	+0.8	
lLi	Input Load Current	Vin = 0 V to Vcc		1.0	ν μΑ	
ILO	Output Leakage Current				5.0	· · · · · ·
lcc1	Vcc Active Current	CE = V _{IL} , f = 5 MHz C/I Devices			5.0	μA mA
	(Note 3)	OUT = 0 mA	E/M Devices		60	WA.
lcc2	Vcc TTL Standby	CE = VIH			1.0	mA
lcc3	Vcc CMOS Standby	<u>CE</u> = V _{cc} ± 0.3 V			100	<u>Α</u>
IPP1	VPP Current During Read	CE = OE = VIL, VPP = V		100	μ Α	

Notes:

- 1. V_{CC} must be simultaneously or before V_{PP} , and removed simultaneously or after V_{PP} .
- 2. Caution: The Am27C4096 must not be removed from (or inserted into) a socket when Vcc or VPP is applied.
- 3. I_{CC1} is tested with $\overline{OE} = V_{IH}$ to simulate open outputs.
- 4. Minimum DC Input Voltage is -0.5 V during transitions, the inputs may overshoot -2.0 V for periods less than 20 ns. Maximum DC Voltage on output pins is $V_{\rm CC}$ +0.5 V, which may overshoot to $V_{\rm CC}$ +2.0 V for periods less than 20 ns.

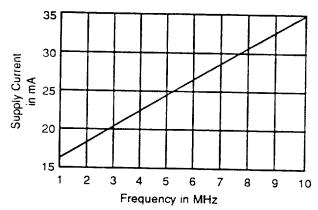


Figure 1. Typical Supply Current vs. Frequency Vcc = 5.5 V, T = 25°C

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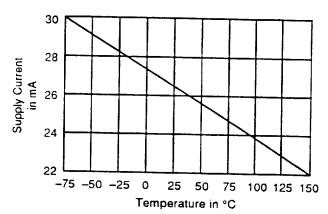


Figure 2. Typical Supply Current vs. Temperature Vcc = 5.5 V, f = 5 MHz

15573B-6

CAPACITANCE

Parameter	Parameter	Test	CD	V040	CLV	/044	PD	040	PL	044	
Symbol	Description	Conditions	Тур	Max	Тур	Max	Тур	Max	Тур	Max	Unit
Cin	Input Capacitance	$V_{IN} = 0 V$	10	13	10	13	6	8	10	13	ρF
Cout	Output Capacitance	V _{OUT} = 0 V	10	13	13	15	8	10	12	14	pF

Notes:

Switching CHARACTERISTICS over operating range unless otherwise specified. (Notes 1, 3 and 4) (for APL Products, Group A, Subgroups 9, 10 and 11 are tested unless otherwise noted)

Paramet	er Symbols						Am27	C4096			
JEDEC	Standard	Parameter Description	Test Conditions		-95	-105	-120	-150	-200	-255, -250	Unit
Avav	tacc	Address to Output Delay	CE = OE	Min	_		-	_		-	
			= V _{IL}	Max	90	100	120	150	200	250	ns
telav	tce.	Chip Enable to	OE = V,L	Min	_		_	_	_	_	
		Output Delay		Max	90	100	120	150	200	250	ns
tGLOV	toe	Output Enable to	CE = V _{IL}	Min	-	-	_	_	_	_	
		Output Delay		Max	50	50	50	5 5	60	60	ns
t _{EHOZ} , t _{GHOZ}	t _{0F} (Note 2)	Chip Enable HIGH or Output Enable HIGH,		Min	-	-	-	-	-	_	
		whichever comes first, to Output Float		Max	30	30	40	40	40	60	ns
taxax	tон	Output Hold from Addresses, CE, or OE, whichever		Min	0	0	0	0	0	0	
		ocurred first		Max	-	-	_	_	_	-	ns

Notes:

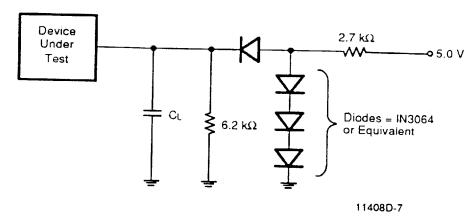
- 1. V_{CC} must be applied simultaneously or before V_{PP} and removed simultaneously or after V_{PP} .
- 2. This parameter is only sampled and not 100% tested.
- 3. Caution: The Am27C4096 must not be removed from (or inserted into) a socket or board when VPP or VCC is applied.
- Output Load: 1 TTL gate and C_L = 100 pF Input Rise and Fall Times: 20 ns

Input Pulse Levels: 0.45 V to 2.4 V

Timing Measurement Reference Level — Inputs: 0.8 V to 2.0 V Outputs: 0.8 V to 2.0 V

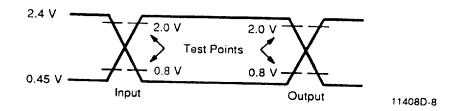
^{1.} This parameter is only sampled and not 100% tested.

SWITCHING TEST CIRCUIT



CL = 100 pF including jig capacitance

SWITCHING TEST WAVEFORM



AC Testing: Inputs are driven at 2.4 V for a Logic "1" and 0.45 V for a Logic "0". Input pulse rise and fall times are ≤ 20 ns.

Am27C4096

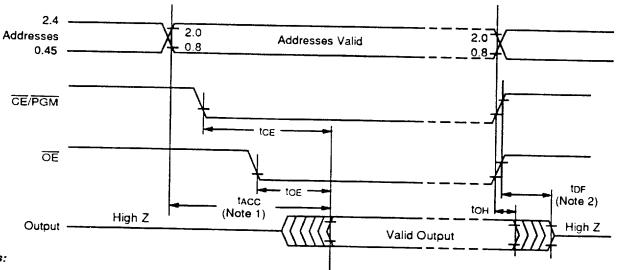
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KEY TO SWITCHING WAVEFORMS

WAVEFORM	INPUTS	OUTPUTS
	Must be Steady	Will be Steady
	May Change from H to L	Will be Changing from H to L
	May Change from L to H	Will be Changing from L to H
	Don't Care, Any Change Permitted	Changing, State Unknown
>>	Does Not Apply	Center Line is High- Impedance "Off" State

KS000010

SWITCHING WAVEFORM



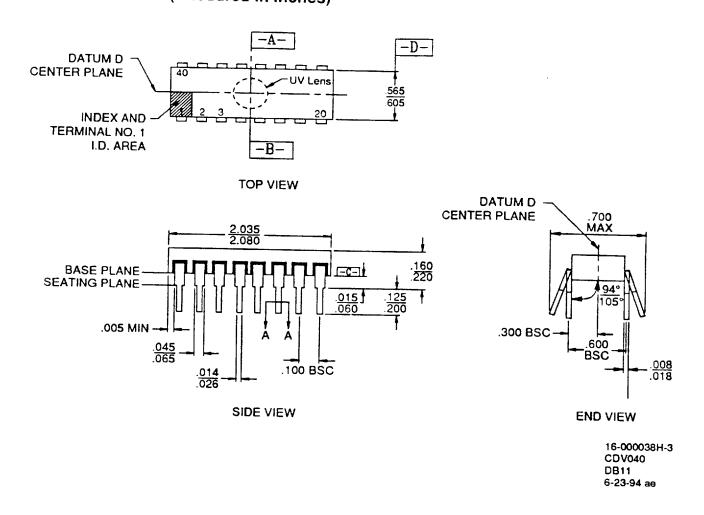
Notes:

- 1. OE may be delayed up to tACC tOE after the falling edge of the addresses without impact on tACC.
- 2. top is specified from OE or CE, whichever occurs first.

11408D-9

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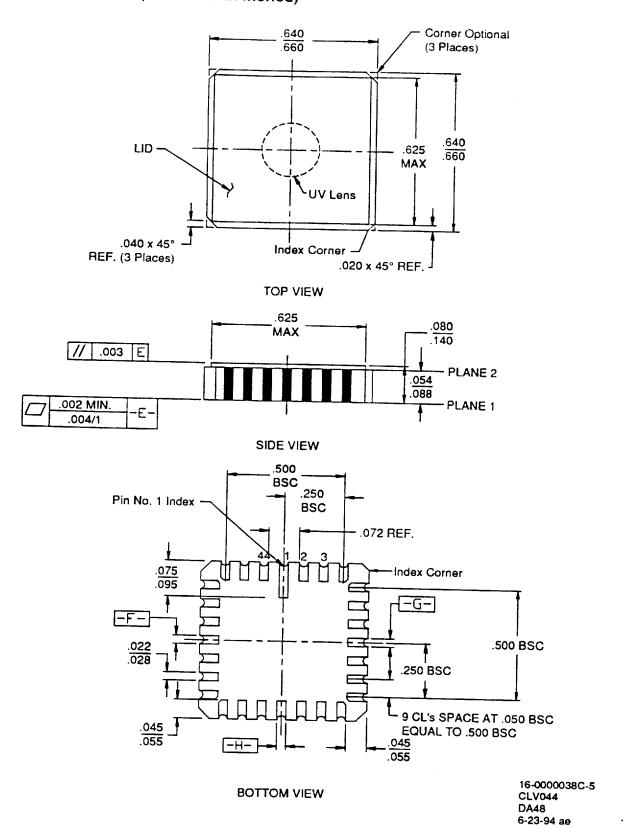
PHYSICAL DIMENSIONS* CDV040 40-Pin Ceramic DIP (measured in inches)



*For reference only. BSC is an ANSI standard for Basic Space Centering.

CLV044

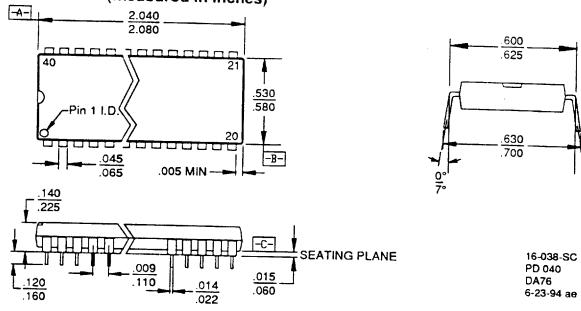
44-Pin Ceramic DIP (measured in inches)



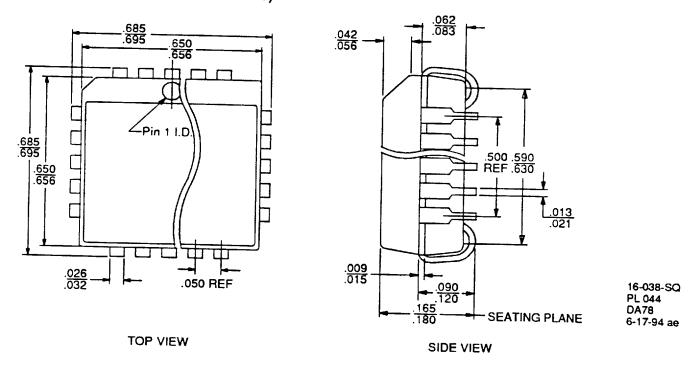
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PD 040

40-Pin Plastic DIP (measured in inches)



PL 044 44-Pin Square Plastic Leaded Chip Carrier (measured in inches)



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